



#### 60V PNP LOW VCESAT TRANSISTOR IN PowerDI3333-8

#### Features

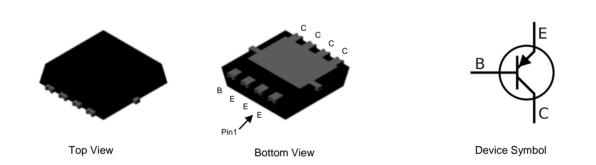
- BV<sub>CEO</sub> > -60V
- Small Form Factor Thermally Efficient Package-Enables Higher Density End Products
- I<sub>C</sub> = -5.5A Continuous Collector Current
- I<sub>CM</sub> = -15A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -70mV @ -1A</li>
- R<sub>SAT</sub> = 39mΩ for a Low Equivalent On-Resistance
- hFE Specified Up to -10A for a High Gain Hold Up
- Complementary NPN Type: DXTN03060BFG
- Rated to +175°C Ideal For High Temperature Environment
- Wettable Flank For Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

# Mechanical Data Case: PowerDI<sup>®</sup>3333-8

- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.03 grams (Approximate)

#### Applications

- Motor Driving
- Line Switching
- High Side Switches



#### Ordering Information (Note 4)

Pa	art Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXT	P03060BFG-7	2J7	7	12	2,000
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

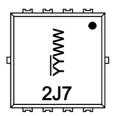
<1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

#### **Marking Information**

PowerDI3333-8 (SWP) (Type UX)

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 $\begin{array}{l} 2J7= \mbox{ Product Type Marking Code} \\ \hline \hline YY WW = \mbox{ Date Code Marking} \\ \hline YY = \mbox{ Last Two Digits of Year (ex: 19 = 2019)} \\ WW = \mbox{ Week Code (01 to 53)} \end{array}$ 



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	lc	-5.5	А
Peak Pulse Current	ICM	-15	А

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
	(Note 5)		1.07	W
Power Dissipation	(Note 6)	PD	2.3	W
	(Note 7)		3.4	W
	(Note 5)		140	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	65	°C/W
	(Note 7)		44	°C/W
Thermal Resistance, Junction to Leads (Note 8	R <sub>θJL</sub>	6	°C/W	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C	

#### ESD Ratings (Note 9)

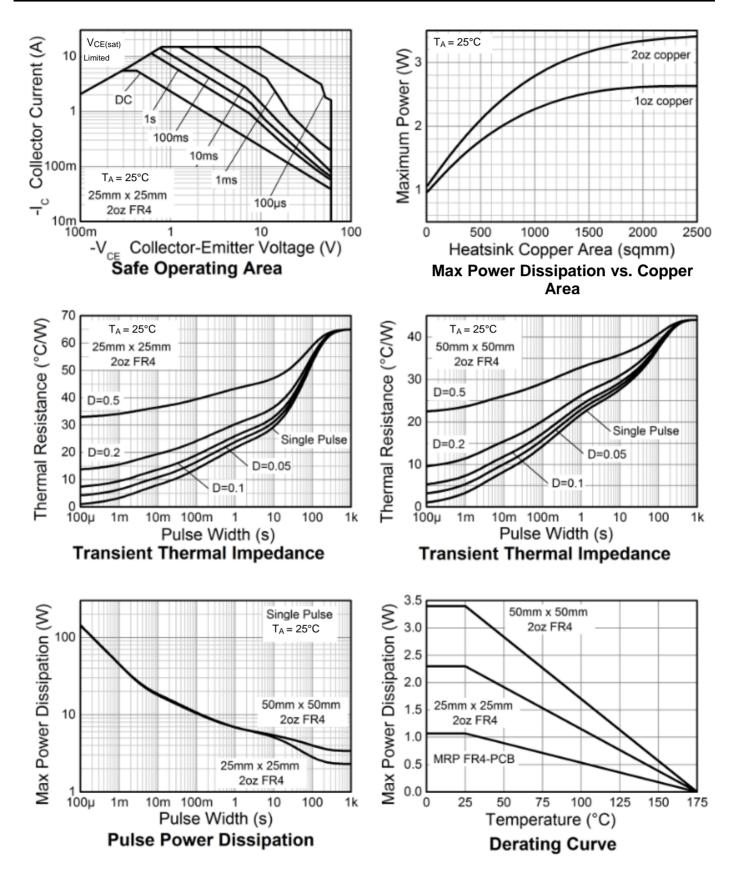
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С
Notes: 5. For a device mounted with the collector tab on MRP FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.				

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For a device mounted with the collector tab on MKP FR-4 PCS; device is meas
 Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 Same as Note 5, except the device is mounted on 50mm x 50mm zoz copper.
 Thermal resistance from junction to solder-point (at the collector tab).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**





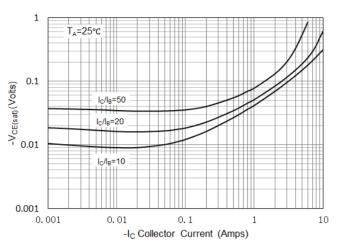
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-100	-120	_	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	-100	-113	—	V	$I_{C} = -1\mu A, R_{B} \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	-60	-77	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.5	_	V	I <sub>E</sub> = -100μA
Collector-Base Cutoff Current	I <sub>CBO</sub>	_	-2	-20	nA	V <sub>CB</sub> = -80V
Collector-Base Cutor Current			_	-100	μA	V <sub>CB</sub> = -80V, T <sub>A</sub> = +125°C
Collector Emitter Cutoff Current ( $D < 1/Q$ )		—	-2	-50	nA	V <sub>CB</sub> = -80V
Collector-Emitter Cutoff Current ( $R \le 1k\Omega$ )	ICER		_	-100	μA	V <sub>CB</sub> = -80V, T <sub>A</sub> = +125°C
Emitter Cutoff Current	I <sub>EBO</sub>	_	-1	-20	nA	$V_{EB} = -6V$
		100	207	—		I <sub>C</sub> = -10mA, V <sub>CE</sub> = -2V
Statia Forward Current Transfer Datia (Nate 10)	hfe	100	161	300	_	$I_{C} = -2A, V_{CE} = -2V$
Static Forward Current Transfer Ratio (Note 10)		45	77	_	_	$I_{C} = -5A, V_{CE} = -2V$
		10	25	—	—	I <sub>C</sub> = -10A, V <sub>CE</sub> = -2V
	V <sub>CE(sat)</sub>	—	-12	-25	mV	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA
Collector Emitter Coturnation Mathema (Nate 40)			-41	-70	mV	I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA
Collector-Emitter Saturation Voltage (Note 10)			-70	-120	mV	I <sub>C</sub> = -2A, I <sub>B</sub> = -200mA
			-150	-250	mV	I <sub>C</sub> = -5A, I <sub>B</sub> = -500mA
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	_	-1000	-1150	mV	I <sub>C</sub> = -5A, I <sub>B</sub> = -500mV
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	_	-880	-1020	mV	I <sub>C</sub> = -5A, V <sub>CE</sub> = -1V
Output Capacitance	C <sub>obo</sub>	_	48	_	pF	V <sub>CB</sub> = -10V. f = 1MHz
Transition Frequency	fT	_	120	—	MHz	$V_{CE} = -10V$ , $I_C = -100mA$ f = 50MHz
	t <sub>delay</sub>	—	9	—	ns	
Outlink is a Time	t <sub>rise</sub>	—	260	_	ns	$V_{CC} = -10V, I_{C} = -1A$
Switching Time	t <sub>storage</sub>	—	1205	—	ns	$I_{B1} = -I_{B2} = -100 \text{mA}$
	t <sub>fall</sub>	—	181	—	ns	

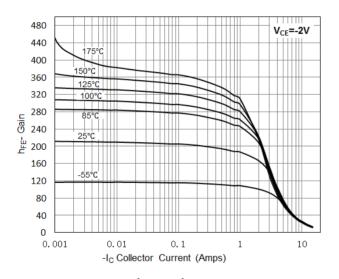
Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



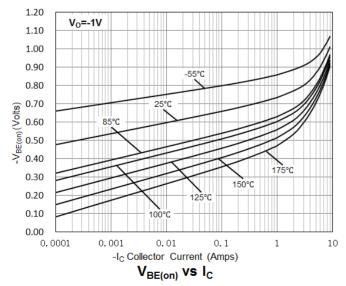
#### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

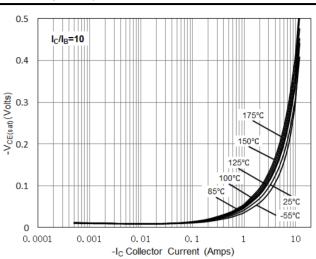




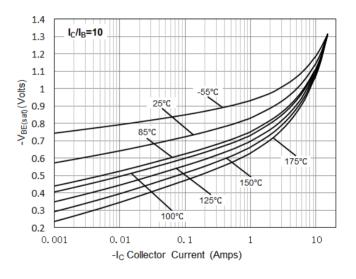








V<sub>CE(sat)</sub> vs I<sub>C</sub>



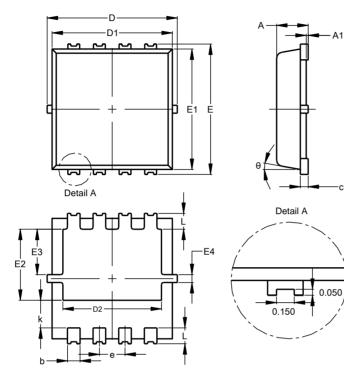
V<sub>BE(sat)</sub> vs I<sub>C</sub>



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)

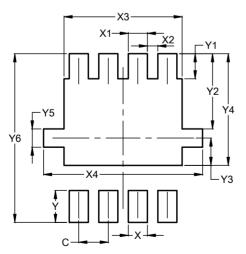


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е			0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

#### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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